

TRANSISTOR(PNP)

FEATURES

High voltage transistor

MARKING:2D

MAXIMUM RATINGS (T_A=25°C unless otherwise noted)



Symbol	Parameter	Value	Units
V _{CB0}	Collector-Base Voltage	-300	V
V _{CEO}	Collector-Emitter Voltage	-300	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-300	mA
P _C	Collector Power Dissipation	300	mW
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C
R _{θJA}	Thermal Resistance, junction to Ambient	410	°C/mW

ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = -100μA, I _E =0	-300		V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = -1mA, I _B =0	-300		V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = -100μA, I _C =0	-5		V
Collector cut-off current	I _{CBO}	V _{CB} =-200V, I _E =0		-0.25	μA
Emitter cut-off current	I _{EBO}	V _{EB} = -5V, I _C =0		-0.1	μA
DC current gain	h _{FE(1)}	V _{CE} = -10V, I _C = -1mA	60		
	h _{FE(2)}	V _{CE} = -10V, I _C =-10mA	100	200	
	h _{FE(3)}	V _{CE} = -10V, I _C =-30mA	60		
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-20mA, I _B = -2mA		-0.2	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = -20mA, I _B = -2mA		-0.9	V
Transition frequency	f _T	V _{CE} =-20V, I _C = -10mA f=30MHz	50		MHz

